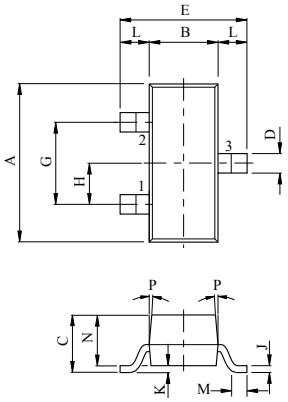
KTC3265

EPITAXIAL PLANAR NPN TRANSISTOR

LOW FREQUENCY POWER AMPLIFIER APPLICATION.
POWER SWITCHING APPLICATION.

FEATURES

- High DC Current Gain : h_{FE}=100～320.
- Low Saturation Voltage
  : $V_{CE(sat)}$=0.4V(Max.) (I_C=500mA, I_B=20mA).
- Suitable for Driver Stage of Small Motor.
- Complementary to KTA1298.
- Small Package.



DIM	MILLIMETERS
A	2.93±0.20
B	1.30+0.20/-0.15
C	1.30 MAX
D	0.45+0.15/-0.05
E	2.40+0.30/-0.20
G	1.90
H	0.95
J	0.13+0.10/-0.05
K	0.00 ~ 0.10
L	0.55
M	0.20 MIN
N	1.00+0.20/-0.10
P	7 °

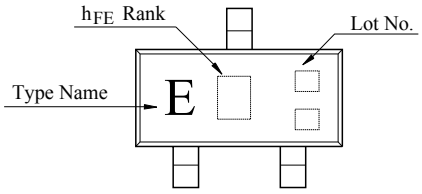
1. EMITTER
2. BASE
3. COLLECTOR

SOT-23

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	35	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	800	mA
Base Current	I_B	160	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55～150	℃

Marking

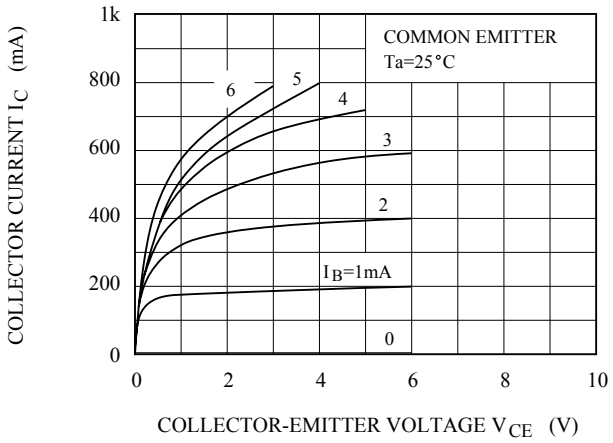


ELECTRICAL CHARACTERISTICS (Ta=25℃)

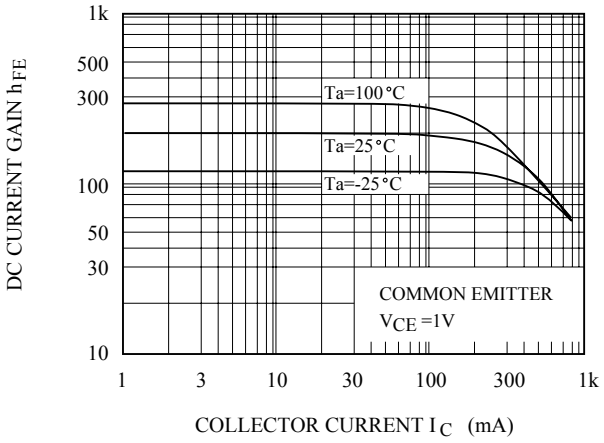
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=30V, I_E=0	-	-	100	nA
Emitter Cut-off Current	I_{EBO}	V_{EB}=5V, I_C=0	-	-	100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V_{EB}=10mA, I_B=0	30	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=1mA, I_C=0	5	-	-	V
DC Current Gain	h_{FE}(1) (Note)	V_{CE}=1V, I_C=100mA	100	-	320	
	h_{FE}(2)	V_{CE}=1V, I_C=800mA	40	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=500mA, I_B=20mA	-	-	0.5	V
Base-Emitter Voltage	V_{BE}	V_{CE}=1V, I_C=10mA	0.5	-	0.8	V
Transition Frequency	f_T	V_{CE}=5V, I_C=10mA, f=100MHz	-	120	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz	-	13	-	pF

Note : h_{FE}(1) Classification O:100～200, Y:160～320

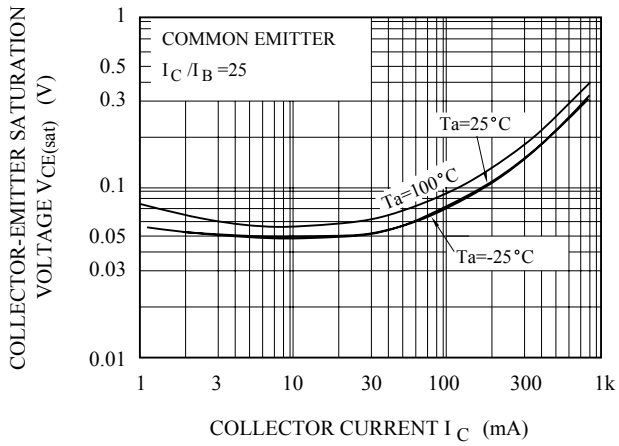
I_C - V_{CE}



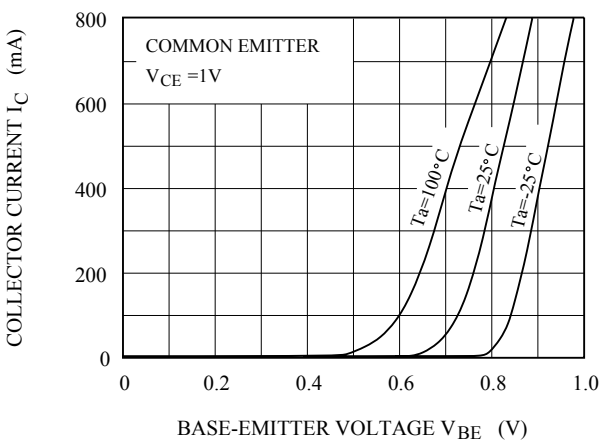
h_{FE} - I_C



$V_{CE(sat)}$ - I_C



I_C - V_{BE}



P_C - Ta

